NPN SILICON RF POWER TRANSISTOR

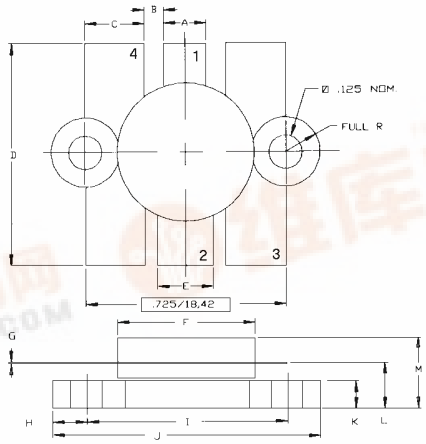
DESCRIPTION:

The **TPV387** is Designed for Operation in Band III TV Transposers and Transmitter Amplifiers from 170 to 230 MHz.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballast Resistors
- Internal Input Matching
- Common Emitter

PACKAGE STYLE 500 6L FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/3,43	.160/4,06
B	.045/1,14	
C	.210/5,33	.220/5,59
D	.835/21,21	.865/21,97
E	.200/5,08	.210/5,33
F	.490/12,45	.510/12,95
G	.003/0,08	.007/0,18
H	.125/3,18	
I	.720/18,29	.730/18,54
J	.970/24,64	.980/24,89
K	.095/2,41	.105/2,67
L	.150/3,81	.170/4,32
M		.280/7,11

1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

MAXIMUM RATINGS

I_C	16 A (CONT)
V_{CE}	35 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.0 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 100 mA	35			V
BV_{CER}	I_C = 100 mA R_{BE} = 10 Ω	60			V
BV_{CBO}	I_C = 50 mA	65			V
BV_{EBO}	I_E = 20 mA	4.0			V
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	20		100	---
C_{ob}	V_{CB} = 30 V f = 1.0 MHz		130	150	pF
G_{PE}	V_{CC} = 28 V P_{out} = 24 W f = 225 MHz	13			dB
y	V_{CC} = 28 V ALL PHASEANGLES f = 225 MHz P_{out} = 24 W LOAD VSWR = ∝:1	NO DEGRADATION IN OUTPUT POWER			
IMD_1	V_{CE} = 28 V Pref = 24 W f = 225 MHz VISION CARRIER = -8 dB SOUND CARRIER = -7 dB SIDEBAND SIGNAL = -16 dB I_E = 3.5 A			-50	dB
P_{oldB}	V_{CC} = 28 V I_Q = 200 mA f = 225 MHz	90			W